

ABSTRACT OF THE DISCLOSURE

In order to provide a nonvolatile semiconductor storage device designed to take off such existing  
5 restraint on the degree of freedom of device design as needed for the purpose of securing design margin, thus realizing a ferroelectric, nonvolatile storage device of high integration density, there is disclosed a capacitor using a ferroelectric thin film is provided, so that the  
10 apparent coercive electric field value in the operational guaranteed margin temperature of the nonvolatile semiconductor storage device when regarded as the voltage applied to the capacitor remains within the range of design margin of the nonvolatile semiconductor storage  
15 device at the coercive electric field value at the specified temperature, in which a metal oxide of a layer structure having the ferroelectric-to-normal dielectric phase transition point of 800°C or higher may be used for the ferroelectric thin film.